

Corrections to “Operation of (111) Ge-on-Insulator n-channel MOSFET Fabricated by Smart-Cut Technology”

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Abstract—Unfortunately, we made the mistake in Fig. 4(b). In Fig. 4(b), the color of (111) and (100) is the opposite. ((111) should be red color, and (100) should be blue color). The correct graph of Figure 4(b) is given here. There is no change in the text.

Index Terms—Ge-on-insulator (GOI), smart-cut technology, (111) surface orientation, MOSFET.

The correct graph of Figure 4(b) is given here. No change is needed in the text.

REFERENCES

- [1] C.-M. Lim, Z. Zhao, K. Sumita, K. Toprasertpong, M. Takenaka, and S. Takagi, “Operation of (111) Ge-on-insulator n-channel MOSFET fabricated by smart-cut technology,” *IEEE Electron Device Lett.*, vol. 41, no. 7, pp. 985–988, Jul. 2020, doi: 10.1109/LED.2020.2999777.

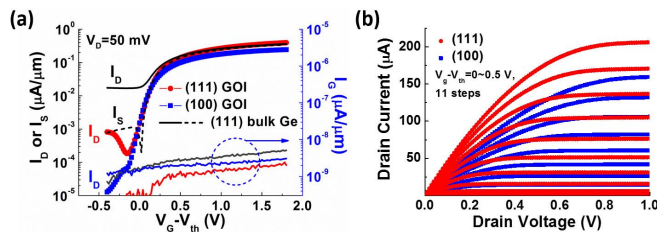


Fig. 4. (a) I_D (or I_S)- V_G and (b) I_D - V_D characteristic of (111) and (100) GOI nMOSFETs.

Manuscript received July 2, 2020; accepted July 2, 2020. Date of current version July 24, 2020. (Corresponding author: Cheol-Min Lim.)

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Digital Object Identifier 10.1109/LED.2020.3007293